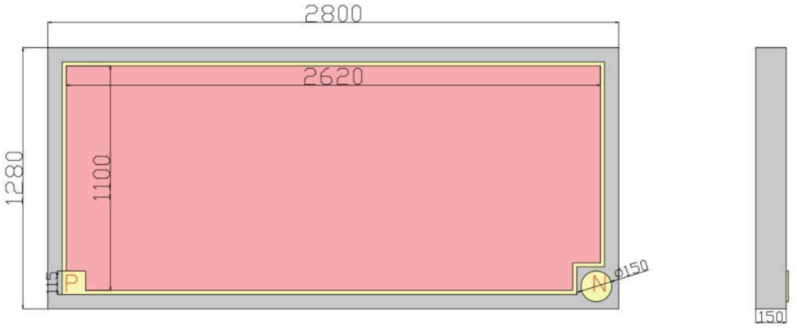
2.8x1.28mm Silicon PIN PD Chip datasheet

P/N ：WS9G-01C



Application

Si PIN photodiode chip

Structure

Planar type：PIN diode

Electrodes：

Top side （Cathode）: Al

Top side (Anode）: Al

DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit
Active	2620 x 1100±15			µm
Chip width	1280			µm
Chip length	2800			µm
Chip height	125	150	175	µm
Pad N(Cathode)		150		µm
Pad P(Anode)		115		µm

Electro-Optical Characteristics (@ Ta=25 ℃)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=10mA, H =0	0.5		1.3	V
Reverse Voltage	V br	Ir =100µA, H =0	35			V
Reverse Dark Current	Id	Vr =10V			10	nA
Sensitive Wavelength Range	λp		400	940	1100	nm
Capacitance	Cj	VR =3V, f=1MHz		20		pF